

ABRIDGED DATA SHEET

DS28C22

DeepCover Secure Memory with I²C SHA-256
and 3Kb User EEPROM

Absolute Maximum Ratings

Voltage Range on Any Pin Relative to GND -0.5V to +4.0V
Maximum Current into Any Pin 20mA
Operating Temperature Range -40°C to +85°C
Junction Temperature +150°C

Storage Temperature Range -55°C to +125°C
Lead Temperature (soldering, 10s) +300°C
Soldering Temperature (reflow) +260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Thermal Characteristics (Note 1)

TDFN

Junction-to-Ambient Thermal Resistance (θ_{JA}) 60°C/W
Junction-to-Case Thermal Resistance (θ_{JC}) 11°C/W

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

Electrical Characteristics

(T_A = -40°C to +85°C, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V _{CC}		2.97	3.3	3.63	V
Supply Current	I _{CC}	(Note 3)			750	μA
		Sleep mode (SLPZ pin low), V _{CC} = 3.63V		0.5	2.0	
SHA-256 Engine						
Computation Current	I _{CSHA}	Refer to the full data sheet.				mA
Computation Time	t _{CSHA}					ms
EEPROM						
Programming Current	I _{PROG}	(Notes 4, 5)	2			mA
Programming Time for 32-Bit Segment	t _{PROG}	Refer to the full data sheet.				ms
Write/Erase Cycling Endurance	N _{CY}	T _A = +85°C (Notes 6, 7)	1000			—
Data Retention	t _{DR}	T _A = +85°C (Notes 8, 9, 10)	10			years
SLPZ Pin						
LOW Level Input Voltage	V _{IL}		-0.5	0.3 x V _{CC}		V
HIGH Level Input Voltage	V _{IH}		0.7 x V _{CC}	V _{CC} + 0.5V		V
Input Leakage Current	I _I	Pin at 3.63V	0.1			μA
Wakeup Time from Sleep Mode	t _{SWUP}	(Note 11)	250			μs
I ² C SCL and SDA Pins (Note 12)						
LOW Level Input Voltage	V _{IL}		-0.5	0.3 x V _{CC}		V
HIGH Level Input Voltage	V _{IH}		0.7 x V _{CC}	V _{CC(MAX)} + 0.5V		V

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Electrical Characteristics (continued)

(T_A = -40°C to +85°C, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Hysteresis of Schmitt Trigger Inputs	V _{HYS}	(Note 4)	0.05 x V _{CC}			V
LOW Level Output Voltage at 3mA Sink Current	V _{OL}				0.4	V
Output Fall Time from V _{IH(MIN)} to V _{IL(MAX)} with Bus Capacitance from 10pF to 400pF	t _{OF}	(Note 4)	60		300	ns
Pulse Width of Spikes Suppressed by the Input Filter	t _{SP}	(Note 4)			50	ns
Input Current with Input Voltage Between 0.1V _{CC(MAX)} and 0.9V _{CC(MAX)}	I _I	(Notes 4, 13)	-10		+10	μA
Input Capacitance	C _I	(Note 4)			10	pF
SCL Clock Frequency	f _{SCL}		0		400	kHz
Hold Time (Repeated) START Condition, After This Period, First Clock Pulse Generated	t _{HD:STA}	(Note 4)	0.6			μs
LOW Period of the SCL Clock	t _{LOW}	(Note 4)	1.3			μs
HIGH Period of the SCL Clock	t _{HIGH}	(Note 4)	0.6			μs
Setup Time for Repeated START Condition	t _{SU:STA}	(Note 4)	0.6			μs
Data Hold Time	t _{HD:DAT}	(Notes 4, 14, 15)			0.9	μs
Data Setup Time	t _{SU:DAT}	(Notes 4, 16)	250			ns
Setup Time for STOP Condition	t _{SU:STO}	(Note 4)	0.6			μs
Bus Free Time Between STOP and START Condition	t _{BUF}	(Note 4)	1.3			μs
Capacitive Load for Each Bus Line	C _b	(Notes 4, 17)			400	pF
Oscillator Warm-Up Time	t _{OSCWUP}	(Note 11)			250	μs

Note 2: Limits are 100% production tested at T_A = +25°C and T_A = +85°C. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization.

Note 3: Operating current continuously reading the Memory/MAC Read/Write Register at 400kHz.

Note 4: Guaranteed by design and/or characterization only. Not production tested.

Note 5: Refer to the full data sheet.

Note 6: Write-cycle endurance is tested in compliance with JESD47G.

Note 7: Not 100% production tested; guaranteed by reliability monitor sampling.

Note 8: Data retention is tested in compliance with JESD47G.

Note 9: Guaranteed by 100% production test at elevated temperature for a shorter time; equivalence of this production test to the data sheet limit at operating temperature range is established by reliability testing.

Note 10: EEPROM Writes can become nonfunctional after the data-retention time is exceeded. Long-term storage at elevated temperatures is not recommended.

Note 11: I²C communication should not take place for the max t_{OSCWUP} or t_{SWUP} time following a power-on reset or a wake-up from sleep mode.

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Electrical Characteristics (continued)

(T_A = -40°C to +85°C, unless otherwise noted.) (Note 2)

Note 12: All I²C timing values are referred to V_{IH(MIN)} and V_{IL(MAX)} levels.

Note 13: I/O pins of the DS28C22 do not obstruct the SDA and SCL lines if V_{CC} is switched off.

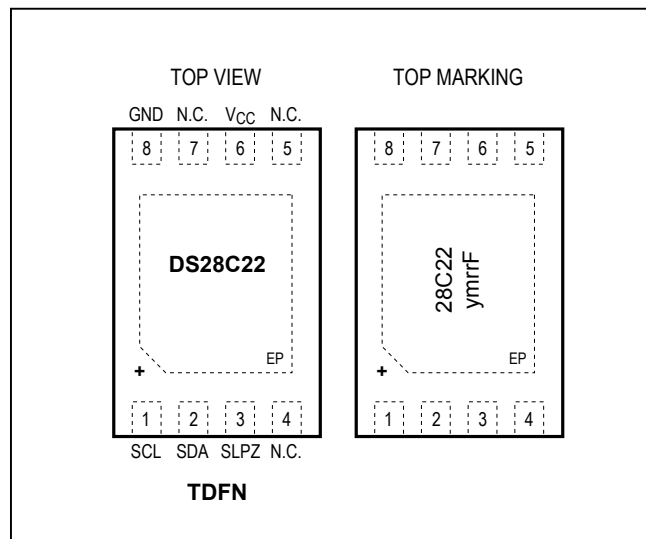
Note 14: The DS28C22 provides a hold time of at least 300ns for the SDA signal (referred to the V_{IH(MIN)} of the SCL signal) to bridge the undefined region of the falling edge of SCL.

Note 15: The maximum t_{HD:DAT} has only to be met if the device does not stretch the LOW period (t_{LOW}) of the SCL signal. If the clock stretches the SCL, the data must be valid by the setup time before it releases the clock. (I²C-bus specification Rev. 03, 19 June 2007)

Note 16: A fast-mode I²C-bus device can be used in a standard-mode I²C-bus system, but the requirement t_{SU:DAT} ≥ 250ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, it must output the next data bit to the SDA line t_{r max} + t_{SU:DAT} = 1000 + 250 = 1250ns (according to the standard-mode I²C-bus specification) before the SCL line is released. Also the acknowledge timing must meet this setup time. (I²C-bus specification Rev. 03, 19 June 2007)

Note 17: C_B = total capacitance of one bus line in pF. The maximum bus capacitance allowable may vary from this value depending on the actual operating voltage and frequency of the application. (I²C-bus specification Rev. 03, 19 June 2007)

Pin Configuration



Pin Description

PIN	NAME	FUNCTION
1	SCL	I ² C Serial Clock Input. Must be connected to V _{CC} through a pullup resistor.
2	SDA	I ² C Serial Data Input/Output. Must be connected to V _{CC} through a pullup resistor.
3	SLPZ	Active-low control input to activate the low-power sleep mode, and to issue a device reset.
4, 5, 7	N.C.	No Connection
6	V _{CC}	Power-Supply Input
8	GND	Ground Reference
—	EP	Exposed Pad. Solder evenly to the board's ground plane for proper operation. Refer to Application Note 3273: <i>Exposed Pads: A Brief Introduction</i> for additional information.

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Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
DS28C22Q+T	-40°C to +85°C	8 TDFN-EP* (2.5k pcs)

+ Denotes a lead(Pb)-free/RoHS-compliant package.

T = Tape and reel.

*EP = Exposed pad.

Package Information

For the latest package outline information and land patterns (footprints), go to www.maximintegrated.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	OUTLINE NO.	LAND PATTERN NO.
8 TDFN-EP	T823+1	21-0174	90-0091

Note to readers: This document is an abridged version of the full data sheet. Additional device information is available only in the full version of the data sheet. To request the full data sheet, go to www.maximintegrated.com/DS28C22 and click on **Request Full Data Sheet**.